

DIO59119/A 30V/1.5A High Efficiency Single-cell Li-Ion Battery Charger with Integrated Power Path

Features

- Maximum 30V input
- Build in power path NFETs and Power Switches
- Independent internal two switches with external control
- 500kHz switching frequency operation
- Trickle Current / Constant Current / Constant Voltage Charge Mode with internal compensation
- Final Float Voltage: 4.35V
- Maximum 1.5A Charge Rate
- Up to 92% Efficiency in Buck Mode
- Independent 1A Boost output
- Up to 93% Efficiency in Boost Mode
- Low Quiescent Current: 1µA in Boost Mode
- +/-0.5% cell voltage accuracy
- Charge/discharge/fault status indicator
- Programmable charge current
- DIO59119A: Programmable output voltage
- DIO59119: 5V output boost
- Charge solutions for JEITA
- Bad battery output forbidden
- Dynamic Power Management
- Input Voltage UVLO and OVP
- Boost output Short Circuit Protection
- Available in QFN3*3-20

Descriptions

Both DIO59119A and DIO59119 require a single inductor to implement both buck or boost function. The DCDC converter operates at 500 kHz frequency and can support low cost inductors and capacitors. The DIO59119/A has integrated OVP protection function, tolerating 30V power surge, effectively improving the system reliability.

The DIO59119/A synchronous boost system supports maximum output current of 1A with efficiency of up to 93%. It also supports low quiescent power consumption, which can be as low as 1uA at no load condition.

The DIO59119/A has switch charging technology that supports adjustable charging current of 1.5A with efficiency up to 92%. And the VDPM function is integrated and the typical VDPM threshold is 4.5V. The DIO59119/A has also offered power path MOSFET handling up to 3A current. Both charging and boost function can work independently as needed. DIO59119/A is designed with QFN3*3-20 package.

Applications

- True Wireless Stereo headphones
- Tablet, Portable Media Players
- Electronic cigarettes
- Smart video doorbell

Ordering Information

Order Part Number	Top Marking		TA	Р	ackage
DIO59119ACN20	EJL9A	Green	-40 to 85°C	QFN3*3-20	Tape & Reel, 5000
DIO59119CN20	DEJL9	Green	-40 to 85°C	QFN3*3-20	Tape & Reel, 5000



Pin Assignments





Pin Definitions

Name	Description
VBUS	Charger Input Voltage. Bypass with a 1µF capacitor to PGND.
NC	No connect.
VOUT	System output pin with two capacitors of 22uF to PGND.
SW	Switching Node. Connect to output inductor.
PGND	Power Ground.
AGND	Analog Ground.
АСОК	Open Drain output. When the Vbus voltage is within the range of ACOK (4.5-6.0V), the output is in high impedance.
DIS	Active LOW, boost mode pin
ENG1	Control signal input to internal NMOS gate, which will turn ON connecting OS1 and OD1 pins
ENG2	Control signal input to internal NMOS gate, which will turn ON connecting OS2 and OD2 pins
FB	Boost output Voltage Feedback Pin, just for DIO59119A
STAT	Open-drain output indicating charging status. The IC pulls this pin LOW when charging, and pulses STAT pin when fault.
BAT	Battery Voltage. Connect to the positive (+) terminal of the battery pack. Bypass with a 0.1µF capacitor to GND if the battery is connected through long leads.



NTC	QFN3*3-20	Temperature sensing pin. Pulling to logic HIGH or LOW will disable the charging function.
RSET	Charge current	setting pin, and the chip will be shut down when RSET pin is floating.
OS2	Output pin conr	nected to internal NMOS Source terminal
OD2	Output pin conr	nected to internal NMOS Drain terminal
OS1	Output pin conr	nected to internal NMOS Source terminal
OD1	Output pin conr	nected to internal NMOS Drain terminal

Block Diagram



Figure 2. IC and System Block Diagram for VOUT Adjustable



Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Rating" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other condition beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Parameter	Rating	Unit
VBUS	30	V
VOUT, SW, DIS, NTC, STAT, VBAT, RSET, ENG1/2, OS1/2, OD1/2, ACOK, FB	6	V
VBUS Pin Current Continuous	1.8	А
VOUT Pin Current Continuous	1.5	А
SW Pin Current Continuous	2.5	А
Junction Temperature	-40 to 150	°C
Storage Temperature	-65 to 150	°C
Lead Soldering Temperature, 10 Seconds	260	°C

Recommend Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended Operating conditions are specified to ensure optimal performance to the datasheet specifications. DIOO does not Recommend exceeding them or designing to Absolute Maximum Ratings.

Parameter	Rating	Unit
Supply Voltage	0 to 6.0	V
VOUT, SW, DIS, NTC, STAT, VBAT, RSET, ENG1/2, OS1/2, OD1/2, ACOK, FB	0 to 5.5	V
VBUS Pin Current Continuous	1.5	А
VOUT Pin Current Continuous	1.0	А
SW Pin Current Continuous	2.0	А
Ambient Temperature	-40 to 85	°C
Junction Temperature	-40 to 125	°C



Electrical Characteristics

 V_{IN} = 5V, T_A = 25°C, unless otherwise specified.

SymbolParameterTest ConditionsMinTypMaxBias Supply (VIN) V_{N} Supply voltage4.55.5 V_{WN} Supply voltage V_{N} rising and measured from V_{N} to GND4.55.5 ΔV_{UNLO} Adapter OK voltage hysteresisMeasured from V_N to GND2.00 ΔV_{UVLO} Input overvoltage protection hysteresis V_{M} rising and measured from V_N to GND5.826.06.2 ΔV_{OVP} Input overvoltage protection hysteresisMeasured from V_N to GND2.005.826.06.2 ΔV_{OVP} Input overvoltage protection hysteresisMeasured from V_N to GND2.005.826.06.2 ΔV_{OVP} Input overvoltage protection hysteresisMeasured from V_N to GND2.005.826.06.2 $Power Supplies$ $V_{BUS} V_{SUS(mni)}$: PVM Enabled, Not Switching0.25.55.55.5 I_{NEUS} V_{SUS} Current $V_{SUS} V_{SUS(mi)}$: PVM Enabled, Not Switching0.25.515 I_{NEUS} V_{SUS} Current in High-Impedance Mode $P_{CT}_{J<85^{\circ}C}, V_{SAT}=4.2V, V_{SUS}=0V$ 1.515 U_{RET} Float Voltage $T_{A}=25^{\circ}C$ -0.50.50.5 V_{OREG} Float Voltage Accuracy $T_{A}=25^{\circ}C$ -0.50.50.5 V_{OREG} Deglitch Time V_{BAT} Falling Below V_{RCH} Threshold30500 O_{RCH} Deglitch TimeV_{BAT} Falling Below V_{RCH} Threshold	$V_{IN} = 5V$, $I_A = 25^{\circ}C$, unless otherwise specified.				
$\begin{tabular}{ c c c c c c } \hline V_{N} & Supply voltage & V_{N} rising and measured from V_{N} to $$ 5.5$ \\ \hline V_{UVLO} & Adapter OK voltage & V_{N} rising and measured from V_{N} to $$ Adapter OK voltage hysteresis & Measured from V_{N} to GND & 200 \\ \hline \Delta V_{UVLO} & Adapter OK voltage protection $$ V_{N} rising and measured from V_{N} to $$ 5.82 & 6.0 & 6.2$ \\ \hline V_{OVP} & Input overvoltage protection $$ hysteresis & Measured from V_{N} to GND & 200 \\ \hline \Delta V_{OVP} & Input overvoltage protection $$ hysteresis & Measured from V_{N} to GND & 200 \\ \hline \hline \Delta V_{OVP} & Input overvoltage protection $$ hysteresis & Measured from V_{N} to GND & 200 \\ \hline \hline Power Supplies & & & & & & & & & & & & & & & & & & &$	Unit				
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$\begin{tabular}{ c c c c c } \hline Adapter OK voltage & GND & 4.5 \\ \hline AV_{UVLO} & Adapter OK voltage hysteresis & Measured from V_N to GND & 200 \\ \hline V_{OVP} & Input overvoltage protection & V_N rising and measured from V_N to & 5.82 & 6.0 & 6.2 \\ \hline AV_{OVP} & Input overvoltage protection & Measured from V_N to GND & 200 \\ \hline AV_{OVP} & Input overvoltage protection & Measured from V_N to GND & 200 \\ \hline Power Supplies & & & & & & & & & & & & & & & & & & &$	V				
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$\begin{tabular}{ c c c c } \hline Charge Voltage Accuracy & $$T_J=0$ to $125^{\circ}C$ & -1 & 1 \\ \hline $$T_J=0$ to $125^{\circ}C$ & -1 & 1 \\ \hline $$M_{RCH}$ & $$Recharge Voltage & $$V_{BAT}$ Falling Below V_{RCH}$ Threshold & $$30$ & $$0$ \\ \hline $$Deglitch Time$ & $$V_{BAT}$ Falling Below V_{RCH}$ Threshold & $$30$ & $$$Oscillator and $$PWM(TBD)$ & $$$VW(TBD)$ & $$$Voltage $$$Voltage $$$Voltage $$$Voltage $$$Voltage $$$Voltage $$$Voltage $$Voltage $$$Voltage $$Voltage $$$Voltage $$$Voltage $$Voltage $$Voltage $$Voltage $$$Voltage $$Voltage $$$	V				
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R _{PP} R _{DS(ON)} of Power Path N-FET Q3+Q4 100	mΩ				
	mΩ				
Reverse Reverse of Low side N-EET 05	mΩ				
R _{OUT1} R _{DS(ON)} of Low side N-FET Q5 500	mΩ				
R _{OUT2} R _{DS(ON)} of Low side N-FET Q6 500	mΩ				
I _{CHG_MAX} Peak current of switching FETs on Charge mode 1.8	A				
Icc Charge current accuracy for Constant Current Mode Icc=1000mA -10 10	%				
ITC Charge current for Trickle Current Mode ITC=100mA 0.1	I _{cc}				



	DIOSSITISIA				
Termination current			0.1		I _{cc}
peration			I		
Feedback voltage for adjustable					Ň
output voltage (for DIO59119A)			1.11		V
	2.5V < V _{BAT} <4.5V,	4 95	5.05	5 15	v
Boost Output Voltage at V _{OUT}	I _{LOAD} from 0 to 200mA	4.00	0.00	0.10	•
(for DIO59119)		4.9	5	5.25	V
	PFM Mode, V _{BAT} =3.6V, I _{OUT} =0		1		uA
Boost, NTC/KEY function and LED indicate total Quiescent Current	PFM Mode, V _{BAT} =3.6V, I _{OUT} =0		15		uA
Boost Mode Shutdown Current			1		uA
Q2 Peak Current Limit			1800		mA
Minimum Battery Voltage for Boost Operation	While Boost Active		2.6		v
UVLO hysteresis	Rising edge		200		mV
DIS, ENG1, ENG2					•
High-Level Input Voltage		1.05			V
Low-Level Input Voltage				0.4	V
STAT Output Low	I _{STAT} =10mA			0.4	V
STAT High Leakage Current	V _{STAT} =5V			1	μA
d Timers			L		
Battery pre-charge threshold	Falling edge		2.5		V
Battery pre-charge hysteresis	Rising edge		100		mV
Battery trickle charge threshold	Falling edge		1.9		V
Battery trickle charge hysteresis	Rising edge		100		mV
Battery trickle charge hysteresis Rising edge 100 Thermal Shutdown Threshold TJ Rising 150					
Hysteresis	T _J Falling		30		°C
					1
High temperature detection			01.67		0/11
voltage threshold	Battery temperature rise		31.25		%V _{BAT}
High temperature detection	Battery temperature drop		2		%V _{BAT}
voltage hysteresis					DAT
Low temperature detection	Battery temperature drop		69		%V _{BAT}
voltage threshold Low temperature detection					
					$%V_{BAT}$
	peration Feedback voltage for adjustable output voltage (for DIO59119A) Boost Output Voltage at Vout (for DIO59119) Boost Mode Quiescent Current Boost, NTC/KEY function and LED indicate total Quiescent Current Boost Mode Shutdown Current Boost Mode Shutdown Current Q2 Peak Current Limit Minimum Battery Voltage for Boost Operation UVLO hysteresis DIS, ENG1, ENG2 High-Level Input Voltage Low-Level Input Voltage STAT Output Low STAT High Leakage Current Battery pre-charge threshold Battery trickle charge threshold Battery trickle charge threshold Battery trickle charge threshold High temperature detection voltage threshold High temperature detection voltage threshold High temperature detection voltage threshold	Peration Feedback voltage for adjustable output voltage (for DIO59119A) 2.5V < V _{BAT} <4.5V, ILOAD from 0 to 200mA Boost Output Voltage at V _{OUT} (for DIO59119) 2.5V < V _{BAT} <4.5V, ILOAD from 0 to 200mA Boost Mode Quiescent Current PFM Mode, V _{BAT} =3.6V, I _{OUT} =0 Boost, NTC/KEY function and LED indicate total Quiescent PFM Mode, V _{BAT} =3.6V, I _{OUT} =0 Q2 Peak Current Limit PFM Mode, V _{BAT} =3.6V, I _{OUT} =0 Minimum Battery Voltage for Boost Operation Rising edge UVLO hysteresis Rising edge DIS, ENG1, ENG2 Istar=10mA STAT Output Low Istar=5V STAT Output Low Istar=5V Battery pre-charge threshold Falling edge Battery trickle charge hysteresis Rising edge Battery trickle charge hysteresis Rising edge Battery trickle charge threshold Falling edge Battery trickle charge hysteresis Rising edge High temperature detection voltage threshold T _J Falling High temperature detection voltage threshold Battery temperature drop High temperature detection voltage threshold Battery temperature drop	Termination current Image: constraint of the second se	Termination current 0.1 peration 1.11 Feedback voltage for adjustable output voltage (for DIOS9119A) 1.11 Boost Output Voltage at Vour (for DIOS9119) 2.5V < V_BAT<4.5V, ILOAD from 0 to 200mA 4.95 5.05 Boost Mode Quiescent Current PFM Mode, V_BAT<3.6V, Iour=0	Termination current0.1perationFeedback voltage for adjustable output voltage (for DIOS9119A)1.11Boost Output Voltage at Vour (for DIOS9119)2.5V < VBAT<4.5V, ILCAD from 0 to 200mA4.955.055.15Boost Mode Quiescent CurrentPFM Mode, VBAT<3.6V, IDUT=0

30V High Efficiency Single-cell Li-lon 1.5A Bi-Direction Charger with Power Path



Application Diagram



Figure 3. IC application Diagram for VOUT Adjustable

Detailed Description

Overview

The DIO59119/A is an integrated solution with both cradle battery charger and headphone battery charger unit. It only needs one single inductor to realize both buck and boost function. DIO59119/A Integrated 2 independent controlled MOSFET to shut down the headphone charging loop to minimize the stand-by current when headphone is fully charged but still placed in the cradle. Please refer to the reference circuit for details.

The charger also comes with a full set of safety features: JEITA Temperature Standard, Over-Voltage Protection, VDPM, Safety Timers, Adaptor ACOK, and ISET short protection. All of these features and more are described in detail below.

Application Information

Dynamic Power Management

For the application of charging and discharging at the same time, Power-Path FET Q3 and Q4 can handle the current greater than 3A.

Power-Down or Under-voltage Lockout (UVLO)

The DIO59119/A is in power down mode when the Vbus is lower than UVLO threshold. The part is considered "dead" and all the terminals are high impedance, at the same time, the ACOK pin output will be pulled down to logic LOW.



Adaptive Input Current Limit Principle (VDPM)

DIO59119/A has adaptive input current limit function. When the input voltage drops to be lower than 4.5V, input current and I_{CHGREF} will be reduced until input voltage recovers back.

Overvoltage-Protection (OVP)

When the V_{BUS} exceeds VBUS_{OVP}, the IC, turns off Q3 and Q4, at the same time, the ACOK pin is pulled down. When V_{BUS} falls about 200mV below VBUS_{OVP}, the fault is cleared and ACOK pin (open drain) is in high impedance state. Under overvoltage protection, the maximum withstand voltage is up to more than 30V.

Charger Status/Fault Status

The STAT pin indicates the operating condition of the IC and provides a fault indicator for interrupt driven systems.

Charge State	STAT Pin	
No Charging	High Z	
Charging	LOW	
Fault	2Hz Pulse	

Table 1. STAT PIN FUNCTION	Table	TAT Pin Functi	on
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Table 2. Potential Fault Conditions Occurred in Charging Mode

Fault Description
VBUS OVP
Poor Input Source
Battery OVP
Thermal Shutdown
No Battery
NTC protection

ACOK indicator

The ACOK pin indicates the Vbus conditions. When Vbus is within the range of power-good condition, i.e. Vbus: 4.5<Vbus<6.0V, the ACOK output is in high impedance. When Vbus<4.5V or Vbus>6.0V, the output is pulled low. The ACOK pin is open drain configuration.

Charge Operation Mode







DIO59119 integrates a complete PWM charging module, shift the charging mode between the trickle charging, constant current charging and constant voltage charging mode with the internal power MOSFET, as shown in Figure 4. The charging current can be adjusted with external resistance, the maximum charging current up to 1.5A. In trickle mode, the chip works in linear charging with a charging current of $0.1 * I_{CC}$. In the constant current mode, the chip charging current is I_{CC} by PWM modulation. In the constant voltage mode, the charging current gradually decreases. Once the charging current below to the charging termination current $0.1 * I_{CC}$, the charging cycle is over. When the battery voltage drops below 4.05V again, the system automatically starts a recharge cycle.

ISET

An external resistor is used to Program the charging current (50 to 1500mA) based on below equation:

I_{BAT} =62000/Rset

(1)

Boost Mode

When pull DIS pin to low and Vbus is absent, the boost circuitry is active. The boost circuitry adopts special circuit to achieve ultra-high efficiency, the highest efficiency can reach more than 93%. Meanwhile, without load the device can draw as low as 1uA quiescent current.

Output Voltage Setting

Boost output voltage can be set by FB pin.

 $V_{OUT} = (R_{HIGH} + R_{LOW}) / R_{LOW} * 1.11$ (2)

Bad Battery Output Forbidden

When DIO59119/A stop providing output voltage to ear pods (such as battery is at UVLO condition or boost is disabled), a pull-down resistor exist at the output pin. The pull-down resistor is about $1K\Omega$ and it always exists even when battery is zero.

Independent control MOSFET (Q5 and Q6)

It integrates two independent MOSFET Q5 and Q6, which can be independently controlled by ENG1 and ENG2 pins. In some design, customer wants to save stand-by current when ear pods are in cradle but Vbus is removed. Customer can use GPIO to control ENG1/ENG2 to turn off the ear pods grounding path to further reduce the stand-by current.

NTC protection

The NTC pin is used for monitoring ambient temperatures.

For example, with properly selected R1 and R2 (see next paragraph for selecting R1/R2), DIO59119 charges the battery within target range (($T_L < T < T_H$). For example, we can set the R1/R2 so that DIO59119 can charge with 100%*Iset between 10°C and 45°C. Between 0°C and 10°C the charge current level is 0.2*I_{SET} and if less than 0°C or more than 45°C, the charging is disabled. T_L and T_H can be adjusted with different R1/R2 combination.

Selecting R1 and R2

The values of R1 and R2 in the application circuit can be determined according to the assumed temperature monitor range and thermistor's values. The Follows is an example: Assume temperature monitor range is $T_L \sim T_H$, $(T_L < T_H)$; the thermistor in battery has negative temperature coefficient (NTC), R_{TL} is thermistor's resistance at T_L , R_{TH} is the resistance at T_H , so $R_{TL} > R_{TH}$, then

At temperature TL, the voltage at TEMP pin is:



 $V_{TEMPL} = \frac{R_2 / R_{TL}}{R_1 + R_2 / R_{TL}} \times V_{CC}$

At temperature TH, the voltage at TEMP pin is:

 $V_{TEMPH} = \frac{R_2 //R_{TH}}{R_1 + R_2 //R_{TH}} \times V_{CC}$

Because:

 $V_{\text{TEMPL}} = V_{\text{HIGH}} = K_2 \times V_{\text{CC}} \ (K_2 = 0.69)$

 $V_{\text{TEMPH}} = V_{\text{LOW}} = K_1 \times V_{\text{CC}} \ (K_1 = 0.3125)$

Then we can have:

 $R_{1} = \frac{R_{TL} \times R_{TH}(K_{2} - K_{1})}{(R_{TL} - R_{TH})K_{1} \times K_{2}}$ $R_{2} = \frac{R_{TL} \times R_{TH}(K_{2} - K_{1})}{R_{TL}(K_{1} - K_{1} \times K_{2}) - R_{TH}(K_{2} - K_{1} \times K_{2})}$

Likewise, for positive temperature coefficient thermistor in battery, we have RTH>RTL and we can calculate:

$$R_{1} = \frac{R_{TH} \times R_{TL}(K_{2} - K_{1})}{(R_{TH} - R_{TL})K_{1} \times K_{2}}$$
$$R_{2} = \frac{R_{TH} \times R_{TL}(K_{2} - K_{1})}{R_{TH}(K_{1} - K_{1} \times K_{2}) - R_{TL}(K_{2} - K_{1} \times K_{2})}$$

We can conclude that temperature monitor range is independent of power supply voltage V_{CC} and it only depends on R1, R2, R_{TL} and R_{TH} : The values of R_{TH} and R_{TL} can be found in related battery handbook or deduced from testing data. In actual application, if only one terminal temperature is concerned (normally protecting overheating), there is no end to use R2 but R1. It becomes very simple to calculate R1 in this case.

Thermal Regulation and Protection

When the IC's junction temperature reaches the T_{CF} (about 120°C), the charger reduces its output current to 550mA to prevent overheating. If the temperature increases beyond $T_{SHUTDOWN}$; charging is suspended, and STAT is pulsed HIGH. In Suspend Mode, all timers stop and the state of the IC's logic is preserved. Charging resumes after the die cools to about 120°C.

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